NCD30S15WCP2

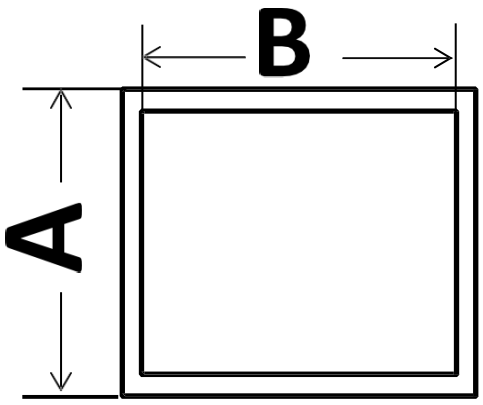
Planar MOS-Controlled Diode Wafer (PMCD)

Maximum Ratings @T_A=25℃ (unless otherwise specified)

Parameter	Symbol	Ratings	Units
Working Peak Reverse Voltage	V_{RWM}	300	V
Average Rectified Forward	$I_{F(AV)}$	15	A
Non-repetitive Peak Surge Current (8.3ms,half sine wave) Rated load (JEDEC METHOD)	I_{FSM}	250	A
Operating Junction Temperature	T_J	175	℃

Electrical Characteristics @T_A=25℃

Parameter	Symbol	Test Condition	MIN.	TYP.	MAX.	Units
Breakdown Voltage	V_{BR}	I_R=0.05mA	300	-	-	V
Forward Voltage Drop	V_F	I_F=10A	-	-	0.89	V
		I_F=15A	-	-	0.95	V
Reverse Leakage Current	I_R	V_R=150V	-	-	10	μA



Item	Information
Die Size (A)	2581 μm
Top Metal Pad Size (B)	2374 μm
Passivation Seal	2511 μm
Wafer Thickness	260 μm
Gross Die Scribe Line Width	70 μm
Top Metal	Al
Back Metal	Ag
Gross Die	2360
Wafer Size	6”